

Description

The MS20H03DF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 30V$ $I_D = 20A$

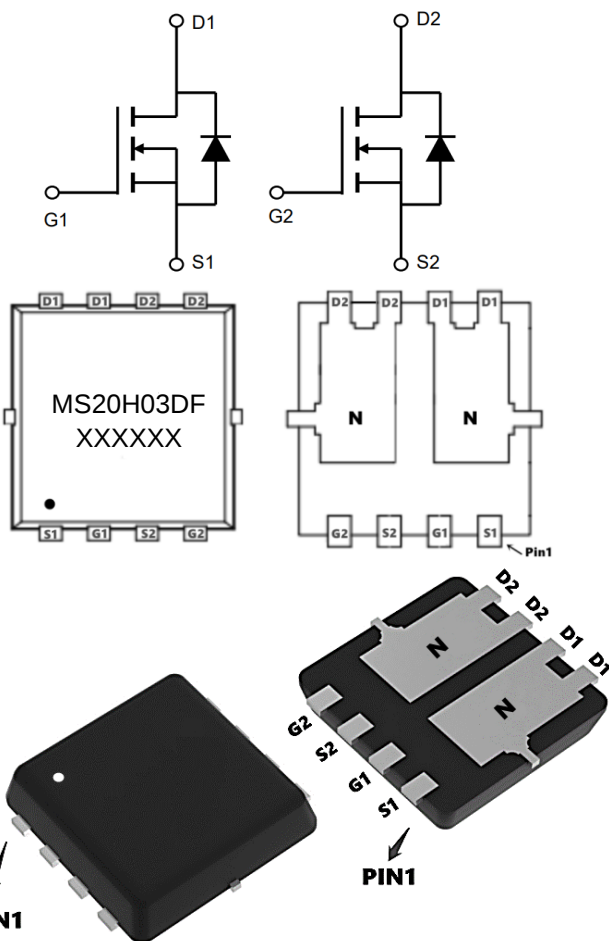
$R_{DS(ON)} < 20m\Omega$ @ $V_{GS}=10V$ (Type: 15m Ω)

Application

Lithium battery protection

Wireless impact

Mobile phone fast charging



Package Marking and Ordering Information

Product ID	Package	Marking	Qty(PCS)
MS20H03DF	PDFN3.3*3.3-8L	MS20H03DF XXXXXX	5000

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^{\circ}C$	Continuous Drain Current	20	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current	9.9	A
I_{DM}	Pulsed Drain Current ²	60	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	85	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	4	$^{\circ}C/W$

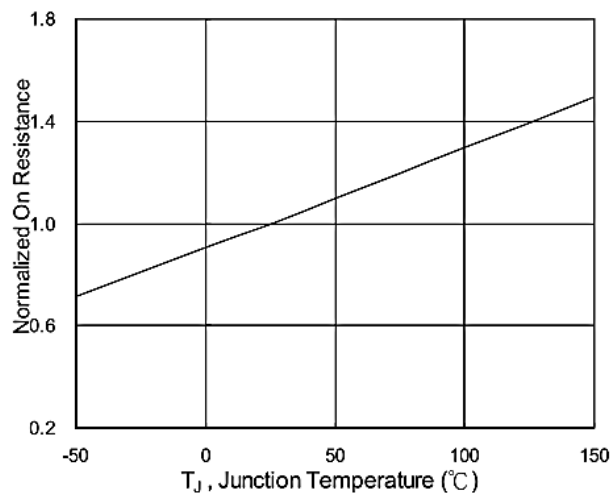
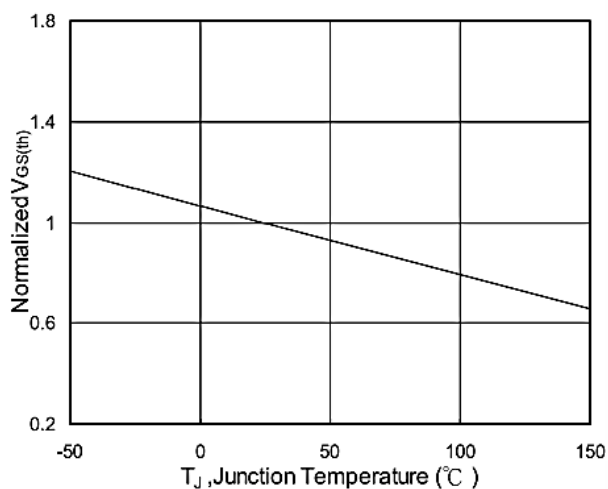
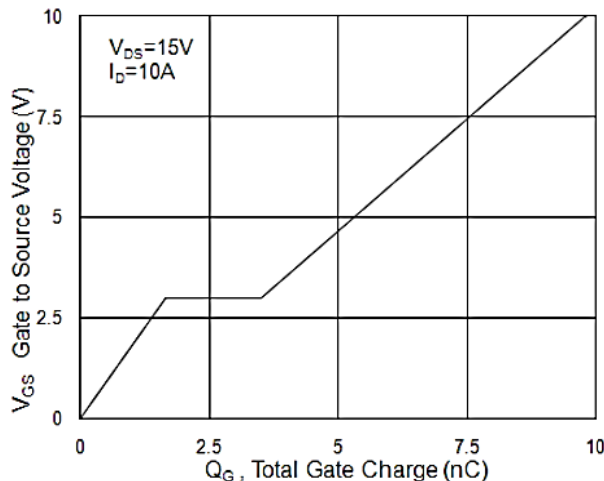
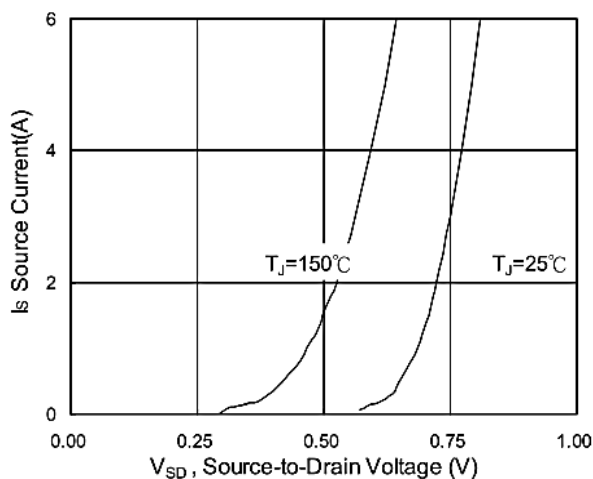
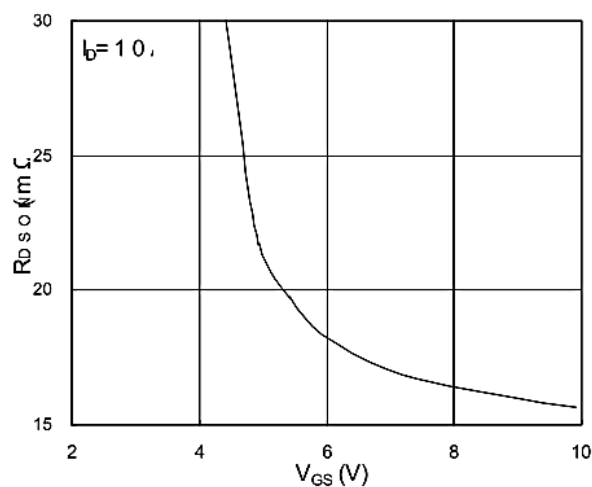
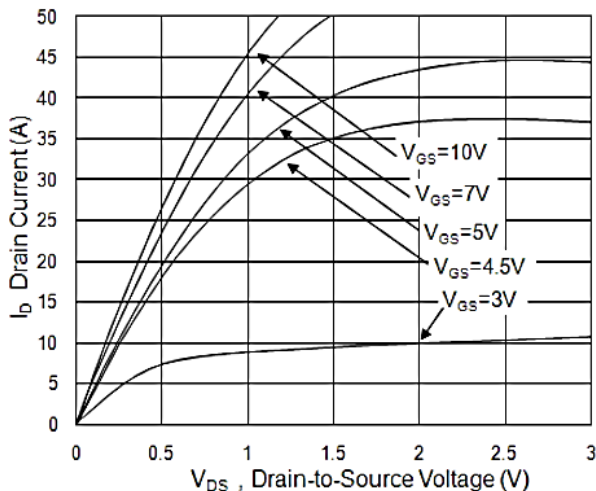
Electrical Characteristics (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	32	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.029	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =5.8A	---	15	20	mΩ
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =5A	---	25	32	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.6	2.5	V
ΔVGS(th)	V _{GS(th)} Temperature Coefficient		---	-2.82	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V, I _D =5A	---	25	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.5	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =5.8A	---	11.5	---	nC
Q _{gs}	Gate-Source Charge		---	1.6	---	
Q _{gd}	Gate-Drain Charge		---	2.9	---	
Td(on)	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3Ω I _D =5A	---	5	---	ns
T _r	Rise Time		---	47.	---	
Td(off)	Turn-Off Delay Time		---	26	---	
T _f	Fall Time		---	8	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	860	---	pF
C _{oss}	Output Capacitance		---	84	---	
C _{rss}	Reverse Transfer Capacitance		---	70	---	
I _s	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	5.8	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、The EAS data shows Max. rating . The test condition is V DD =25V,V GS =10V,L=0.1mH,I AS =12.7A
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Typical Characteristics



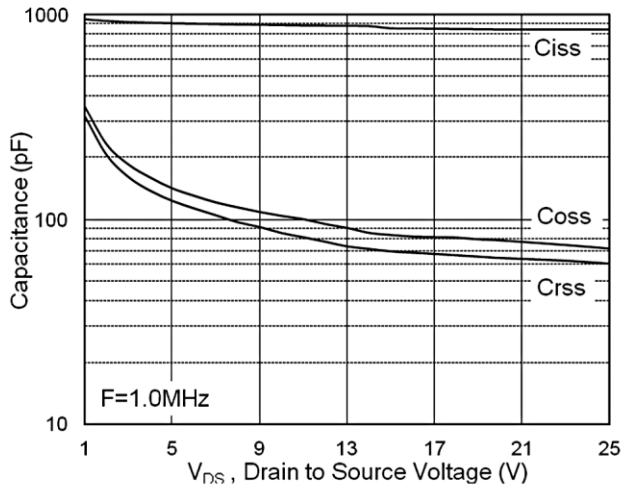


Fig.7 Capacitance

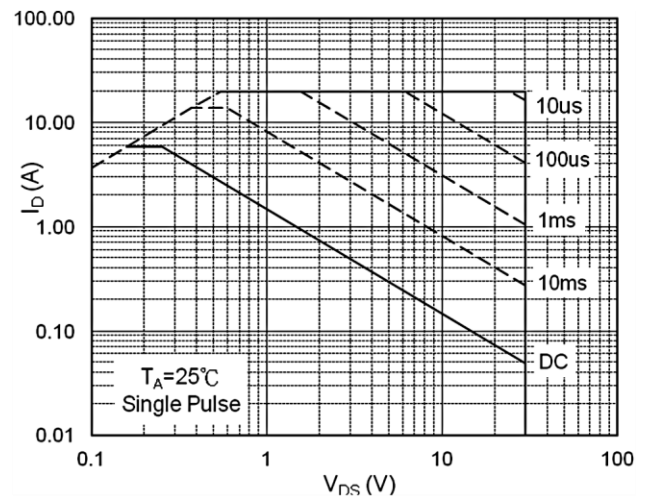


Fig.8 Safe Operating Area

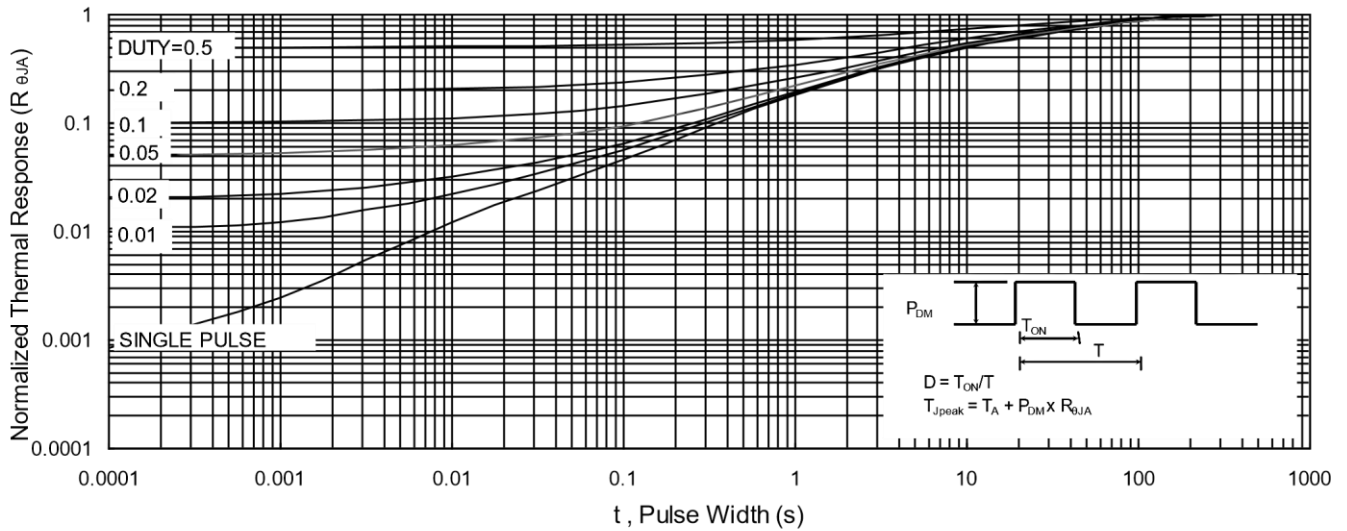


Fig.9 Normalized Maximum Transient Thermal Impedance

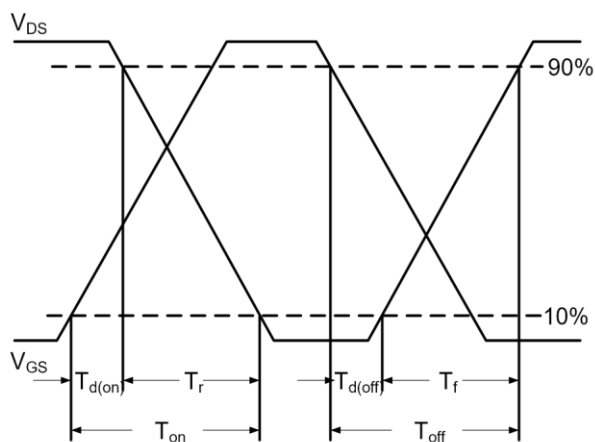


Fig.10 Switching Time Waveform

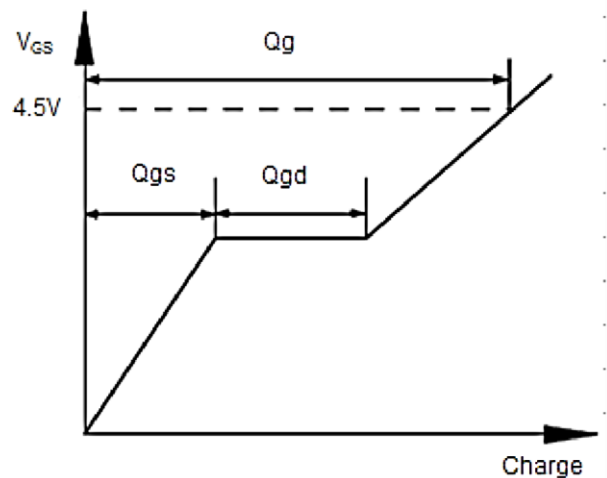
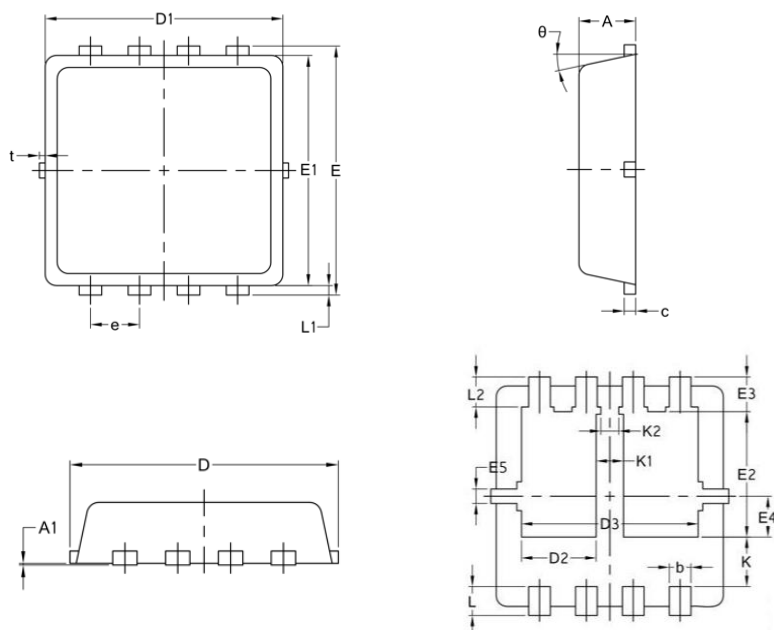


Fig.11 Gate Charge Waveform

Package Mechanical Data PDFN3.3*3.3-8L



Symbol	Common		
	Mm		
	Min	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.25	0.30	0.39
c	0.14	0.152	0.20
D	3.20	3.30	3.45
D1	3.05	3.15	3.25
D2	0.84	1.04	1.24
D3	2.30	2.45	2.60
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.60	1.74	1.90
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.50	0.69	0.80
K1	0.30	0.38	0.53
K2	0.15	0.25	0.35
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
L2	0.27	0.42	0.57
t	0	0.075	0.13
Φ	10°	12°	14°